

UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Hugues Marchand et al. Examiner: Matthew J. Song  
Serial No.: 09/922,122 Group Art Unit: 1765  
Filed: August 3, 2001 Docket: G&C 30794.79-US-U1  
Title: METHOD OF CONTROLLING STRESS IN GALLIUM NITRIDE FILMS  
DEPOSITED ON SUBSTRATES

CERTIFICATE OF MAILING UNDER 37 CFR 1.10

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Date of Deposit: May 16, 2005

I hereby certify that this paper or fee is being deposited with the United States Postal Service 'Express Mail Post Office To Addressee' service under 37 CFR 1.10 and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

By:

Name: 

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT(37 C.F.R. §1.97(c))

MAIL STOP AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

Pursuant to 37 C.F.R. §1.97(c), please charge the amount of \$180.00 to Deposit Account No. 50-0494 of Gates & Cooper LLP for having the items of information listed considered after the mailing date of a first Office Action on-the-merits, but before the mailing date of either a final action under 37 C.F.R. § 1.113, or a Notice of Allowance under 37 C.F.R. § 1.311.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each foreign patent document and each non-patent document listed on the enclosed Form 1449 is provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to

establish that the reference(s) are not "prior art". Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please direct any response or inquiry to the below-signed attorney at (310) 641-8797.

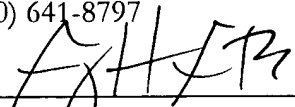
Respectfully submitted,

GATES & COOPER LLP  
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Date: May 16, 2005

GHG/sjm

By:   
Name: George H. Gates  
Reg. No.: 33,500

Form 1449*	Docket Number: G&C 30794.79-US-U1	Application Number: 09/922,122
INFORMATION DISCLOSURE STATEMENT		
Applicant: Hugues Marchand et al.		
Filing Date: August 3, 2001		Group Art Unit: 1765

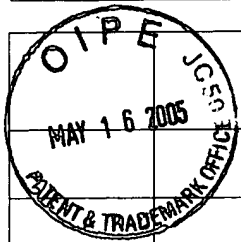
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,880,485	03/09/99	Marx et al.			
	6,153,010	11/28/00	Kiyoku et al.			
	6,180,270	01/30/01	Cole et al.			
	6,291,319	09/18/01	Yu et al.			
	6,328,796	12/11/01	Kub et al.			
	6,358,770	03/19/02	Itoh et al.			
	6,391,748	05/21/02	Temkin et al.			
	6,420,197	07/16/02	Ishida et al.			
	6,440,823	08/27/02	Vaudo et al.			
	6,459,712	10/01/02	Tanaka et al.			
	6,524,932	02/25/03	Zhang et al.			
	6,548,333	04/15/03	Smith			
	6,610,144	08/26/03	Mishra et al.			
	6,707,074	03/16/04	Yoshii et al.			
	6,765,240	07/20/04	Tischler et al.			

FOREIGN PATENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
		Bykhovski, A.D. et al., "Elastic strain relaxation in GaN-AlN-GaN semiconductor - insulator - semiconductor structures," J. Appl. Phys. 78(6):3691-3696, September 15, 1995
		Dadgar, A. et al., "Metalorganic Chemical Vapor Phase Epitaxy of Crack-Free GaN on Si (111) Exceeding 1µm in Thickness," Jpn. J. Appl. Phys. 39:L1183-1185, November 15, 2000
		Lei, T. et al., "Epitaxial growth of zinc blende and wurtzitic gallium nitride thin films on (001) silicon," Appl. Phys. Lett. 59(8):944-946, August 19, 1991
		Guha, S. et al., "Ultraviolet and violet GaN light emitting diodes on silicon," Appl. Phys. Lett. 72(4):415-417, January 26, 1998

EXAMINER:	DATE CONSIDERED:
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	

<b>Form 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b>	Docket Number: G&C 30794.79-US-U1	Application Number: 09/922,122
	Applicant: Hugues Marchand et al.	
	Filing Date: August 3, 2001	Group Art Unit: 1765

	Haffouz, S. et al., "The effect of the Si/N treatment of a nitridated sapphire surface on the growth mode of GaN in low-pressure metalorganic vapor phase epitaxy," Applied Physics Letters, 73(9):1278-1280, August 31, 1998
	Lahreche, H. et al., "Optimisation of AlN and GaN growth by metalorganic vapour-phase epitaxy (MOVPE) on Si(111)," Journal of Crystal Growth, 217:13-25, 2000
	Nikishin, S.A. et al., "High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia," Applied Physics Letters, 75(14):2073-2075, October 4, 1999
	Semond, F. et al., "GaN grown on Si(111) substrate: From two-dimensional growth to quantum well assessment," Applied Physics Letters, 75(1):82-84, July 5, 1999
	Seon, M. et al., "Selective growth of high quality GaN on Si(111) substrates," Applied Physics Letters, 76(14):1842-1844, April 3, 2000
	Ohtani, A. et al., "Microstructure and photoluminescence of GaN grown on Si(111) by plasma-assisted molecular beam epitaxy," Appl. Phys. Lett. 65(1):61-63, July 4, 1994
	Osinsky, A. et al., "Visible-blind GaN Schottky barrier detectors grown on Si(111)," Applied Physics Letters, 72(5):551-553, February 2, 1998
	Tanaka, S. et al., "Defect structure in selective area growth GaN pyramid on (111)Si substrate," Applied Physics Letters, 76(19):2701-2703, May 8, 2000
	Tran, C.A. et al., "Growth of InGaIn/GaN multiple-quantum-well blue light-emitting diodes on silicon by metalorganic vapor phase epitaxy," Applied Physics Letters, 75(11):1494-1496, September 13, 1999
	Zhao, G.Y. et al., "Growth of Si delta-doped GaN by metalorganic chemical-vapor deposition," Applied Physics Letters, 77(14):2195-2197, October 2, 2000
	Zhao, Z.M. et al., "Metal-semiconductor-metal GaN ultraviolet photodetectors on Si(111)," Applied Physics Letters, 77(3):444-446, July 17, 2000

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